VS-2ENH01-M3, VS-2ENH02-M3

Vishay Semiconductors



Ultrafast Rectifier, 2 A FRED Pt[®]



Cathode O Anode

LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS					
I _{F(AV)}	2 A				
V _R	100 V, 200 V				
V _F at I _F	0.79 V				
I _{FSM}	40 A				
t _{rr} (typ.)	23 ns				
T _J max.	175 °C				
Package	SMP (DO-220AA)				
Circuit configuration	Single				

FEATURES

- Very low profile typical height of 1.0 mm
- · Ideal for automated placement
- · Low forward voltage drop, low power losses
- · Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- For PFC, CRM snubber operation
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATION

For use in high frequency, freewheeling, DC/DC converters, PFC, and in snubber industrial and automotive applications.

MECHANICAL DATA

Case: SMP (DO-220AA)

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002, meets JESD 201 class 2 whisker test

Polarity: color band denotes cathode end

ABSOLUTE MAXIMUM RATINGS						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Peak repetitive reverse	VS-2ENH01-M3	V		100	V	
voltage	VS-2ENH02-M3	V _{RRM}		200	v	
Average rectified forward current		I _{F(AV)}	T _C = 158 °C	2	^	
Non-repetitive peak surge current		I _{FSM}	T _J = 25 °C, 10 ms sine pulse	40	A	
Operating junction and storage temperatures		TJ, TStg		-55 to +175	°C	

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage,	VS-2ENH01-M3	V _{BR} ,	1 - 100 110	100	-	-	V
blocking voltage	VS-2ENH02-M3	V _R	l _R = 100 μΑ	200	-	-	
Forward voltage		V _F	I _F = 2 A	-	0.94	1.00	
			I _F = 2 A, T _J = 150 °C	-	0.79	0.84	
Reverse leakage current		1	V _R = V _R rated	-	-	2	
		I _R	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	20	μA
Junction capacitance		CT	V _R = 200 V	-	8	-	pF

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COMPLIANT HALOGEN FREE



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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25 \ ^{\circ}C$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CON	MIN.	TYP.	MAX.	UNITS	
Reverse recovery time t _{rr}		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 1$	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 100 \text{ A}/\mu\text{s}, V_R = 30 \text{ V}$		23	-	
	t _{rr}	$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr} = 0.25 \text{ A}$		-	-	28	
		T _J = 25 °C	I _F = 2 A dI _F /dt = 200 A/µs V _R = 100 V	-	16	-	A
		T _J = 125 °C		-	25	-	
Peak recovery current	I _{RRM}	T _J = 25 °C		-	2.0	-	
		T _J = 125 °C		-	3.1	-	
Reverse recovery charge Q _{rr}	0	T _J = 25 °C		-	15	-	
	Qrr	T _J = 125 °C		-	37	-	10

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	SYMBOL TEST CONDITIONS		TYP.	MAX.	UNITS
Maximum junction temperature ran	0	T _J , T _{Stg}		-55	-	175	°C
Thermal resistance, junction to mount		R _{thJM} ⁽¹⁾	Infinite heatsink	-	7	9	°C/W
Thermal resistar junction to ambi	,	R _{thJA}	R _{thJA} PCB footprint 4.8 mm x 4.8 mm		107	-	0/10
Marking device	VS-2ENH01-M3		Case style SMP (DO-220AA)		21	-11	
warking device	VS-2ENH02-M3		Case style Sivir (DO-220AA)	2H2			

Note

⁽¹⁾ Thermal resistance junction to mount follows JEDEC[®] 51-14 transient dual interface test method (TDIM)

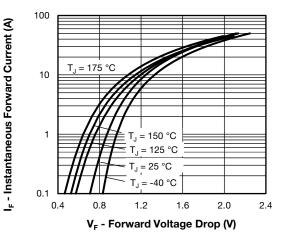


Fig. 1 - Typical Forward Voltage Drop Characteristics

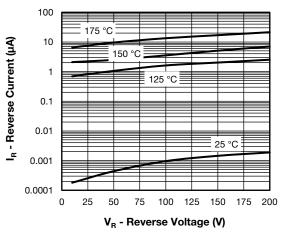


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



VS-2ENH01-M3, VS-2ENH02-M3

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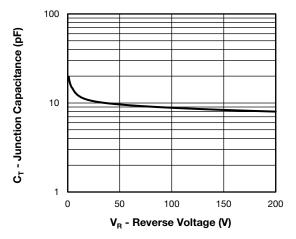


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

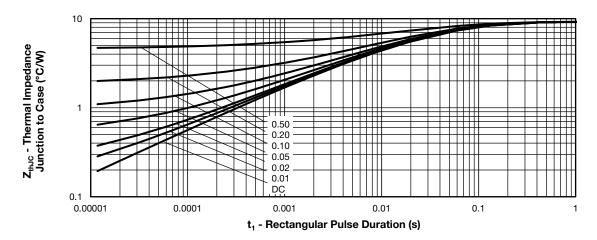


Fig. 4 - Transient Thermal Impedance, Junction to Case

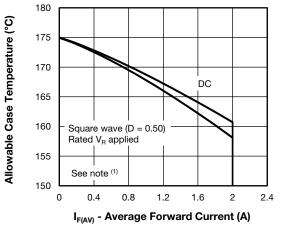


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

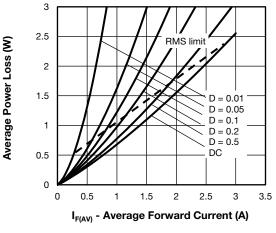


Fig. 6 - Forward Power Loss Characteristics

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125 °C

dl_F/dt (A/µs)

50 45

40

35

30

25

20

15

10

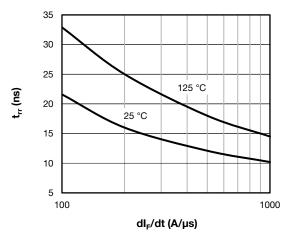
100

Q_{rr} (nC)

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25 °C

1000



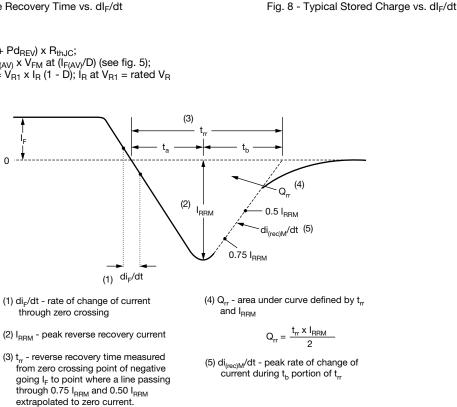
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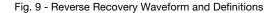
Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

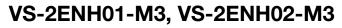
Note

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- ⁽¹⁾ Formula used: $T_C = T_J (Pd + Pd_{REV}) \times R_{thJC}$;
- $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig. 5}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$



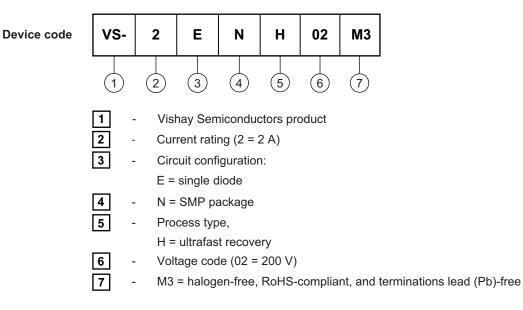




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ORDERING INFORMATION TABLE



ORDERING INFORMATION (Example)						
PREFERRED P/N	PREFERRED PACKAGE CODE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-2ENH01-M3/84A	84A	3000	7" diameter plastic tape and reel			
VS-2ENH01-M3/85A	85A	10 000	13" diameter plastic tape and reel			
VS-2ENH02-M3/84A	84A	3000	7" diameter plastic tape and reel			
VS-2ENH02-M3/85A	85A	10 000	13" diameter plastic tape and reel			

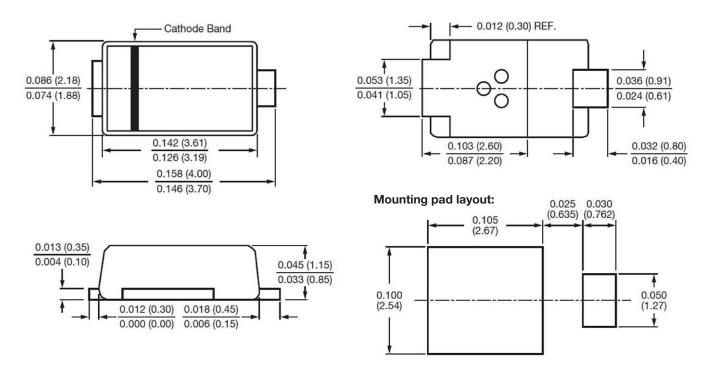
LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?96547					
Part marking information	www.vishay.com/doc?96574				
Packaging information	www.vishay.com/doc?88869				
SPICE model	www.vishay.com/doc?96551				



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SMP (DO-220AA)

DIMENSIONS in inches (millimeters)





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